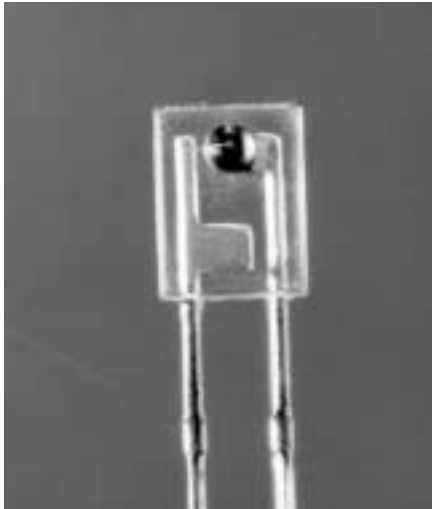


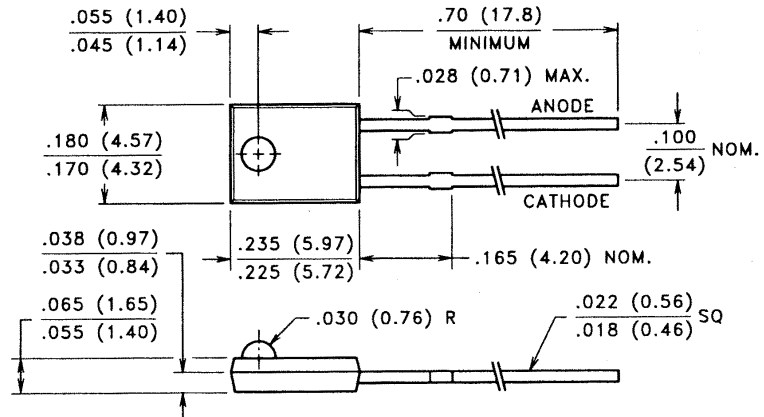
GaAlAs Infrared Emitting Diodes

Molded Lateral Package — 880 nm

VTE7172H, 7173H



PACKAGE DIMENSIONS inch (mm)



CASE 7 LATERAL
CHIP SIZE: .011" x .011"

DESCRIPTION

These side-looking packages are designed for use in PC board mounted interrupt detectors. The package is transfer molded plastic and contains a high efficiency, 880 nm, GaAlAs IRED die.

RoHS Compliant



ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures			
Storage and Operating:	-40°C to 85°C	Maximum Reverse Voltage:	5.0V
Continuous Power Dissipation:	100 mW	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Derate above 30°C:	1.82 mW/°C	Peak Wavelength (Typical):	880 nm
Maximum Continuous Current:	50 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF
Derate above 30°C:	0.91 mA/°C	Response Time @ $I_F = 20$ mA	
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Rise: 1.0 μs Fall: 1.0 μs	
Temp. Coefficient of Power Output (Typ.):	-8%/°C	Lead Soldering Temperature:	260°C
		(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance		Radiant Intensity	Total Power	Test Current	V_F				
	E_e	Condition	I_e	P_O	I_{FT}	@ I_{FT}				
	mW/cm ²	distance	Diameter	mW	mA	Volts				
	Min.	Typ.	mm	mm	Min.	Typ.	Max.	Typ.		
VTE7172H	0.4	0.6	16.7	4.6	1.1	2.5	20	1.3	1.8	$\pm 25^\circ$
VTE7173H	0.6	0.8	16.7	4.6	1.7	5.0	20	1.3	1.8	$\pm 25^\circ$

■ Refer to General Product Notes, page 2.